

Vibrational frequencies of light impurities in silicon

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Abstract

We have developed a formulation of density functional perturbation theory for the calculation of vibrational frequencies in molecules and solids, which uses numerical atomic orbitals as a basis set for the electronic states. The (harmonic) dynamical matrix is extracted directly from the first order change in the density matrix with respect to infinitesimal atomic displacements from the equilibrium configuration. We have applied this method to study the vibrational properties of a number of hydrogen-related complexes and light impurities in silicon. The diagonalization of the dynamical matrix provides the vibrational modes and frequencies, including the local vibrational modes (LVMs) associated with the defects. In addition to tests on simple molecules, results for interstitial hydrogen, hydrogen dimers, vacancy-hydrogen and self-interstitial-hydrogen complexes, the boron-hydrogen pair, substitutional C, and several O-related defects in c-Si are presented. The average error relative to experiment for the ~ 60 predicted LVMs is about 2% with most highly harmonic modes being extremely close and the more anharmonic ones within 5-6% of the measured values.

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I. INTRODUCTION

The knowledge of the structures of impurities and defects is an essential prerequisite for understanding the electrical and optical changes that these complexes induce in semiconductors such as crystalline silicon^{1,2}. The presence of light impurities such as H, B, C or O, results in the appearance of infra-red (IR) or Raman active local vibrational modes (LVMs) usually well isolated from the frequency range of the phonons of the host material. The observation of LVMs coupled with isotope substitutions and uniaxial stress measurements provide precious information about the type and number of impurity atoms involved and the symmetry of the defect. However, these data are rarely sufficient to identify unambiguously the defect. Since the early days of Stein³, a large number of vibrational modes have been identified through the interplay of experiment and theory.

The calculation of LVMs at the *ab-initio* level provides a critical link between theory and experiment. This is particularly true in the case of hydrogen, since it binds covalently in the immediate vicinity of many impurities and defects thus giving rise to a number of LVMs in the range ~ 800 to ~ 2200 cm^{-1} . Other common impurities in Si which produce LVMs are B, C, O, but any element lighter than Si can in principle be observed by LVM spectroscopy.

The computation of systematically accurate vibrational frequencies is a challenge for first principles theory, given their sensitivity on details of bonding geometry and electronic structure. Typical accuracies in the calculated vibrational modes for light impurities in silicon in former works are within 3-10% of the experimental data, which means in some cases a deviation of over 100 cm^{-1} .

Various approaches have been used to calculate LVMs, from semiempirical models⁴, to *ab-initio* Hartree-Fock⁵ and density functional theory^{6,7,8}. In most cases, frequencies are calculated in the spirit of the *frozen phonon* approximation. One computes the total energy of the system in the equilibrium configuration (that in which the forces acting on the atoms are zero) and then for small displacements of selected atoms (either individually or in the direction of a normal mode, if this is known). The actual value of the atomic displacement (typically a few hundredths of an Å) and the response of the nearby atoms are parameters chosen by the user. One can either fit the energy vs. displacement to a polynomial and extract a specific vibrational mode^{6,9}, or compute the dynamical matrix by finite differences⁷. When a few specific modes is all that is needed, only the movement of the atoms involved

in those modes is considered. In these methods, it is not possible to completely isolate the harmonic contributions from the anharmonic ones, since finite displacements always involve some anharmonic effects. For this reason, the frequencies obtained in this approach are sometimes referred to as *quasi-harmonic*¹⁰.

One can also calculate vibrational properties from constant-temperature molecular-dynamics simulations, for instance by extracting selected frequencies from the velocity-velocity autocorrelation function¹¹ or by using more sophisticated spectral estimators, like the Multiple Signal Classification (MUSIC) algorithm.^{12,13} This is computationally exhausting, since long molecular dynamics runs are required, but potentially very accurate.¹³ This also allows the calculation of frequencies as a function of temperature.

However, the calculation of vibrational frequencies does not necessarily require the actual displacement of the atoms, as in the methods described above. Linear response theory (in particular through the application of perturbation theory in density functional theory) has been thoroughly used in the past¹⁴ to compute the response of the system to infinitesimal atomic displacements, and from that, the vibrational frequencies in the harmonic approximation. This can be done with the only knowledge of the electronic solution in the equilibrium configuration. The advantage of this approach is that anharmonic effects are eliminated, and that no reference is needed to explicit finite atomic displacements. Besides, this approach allows to compute phonons with arbitrary $\mathbf{q}$ vector in crystalline systems, without having to consider a supercell commensurate with the periodicity of the phonon, as it is required in the frozen phonon and molecular dynamics approaches.

We propose a method, based on density functional perturbation theory (DFPT), to compute vibrational frequencies in the harmonic approximation. We use a basis set of numerical atomic orbitals to expand the electronic wavefunctions, which makes the method computationally very efficient, and allows us to calculate systems with a large number of atoms. We have applied it to make a systematic study of a number of defect centers in silicon, involving light impurities and their complexes with intrinsic defects (vacancies and self-interstitials). In most cases, the comparison of the calculated and measured vibrational frequencies is very favorable, improving on the results obtained by other approaches.

The outline of this paper is as follows. We first discuss the theoretical method and the model used to describe the defects. Then we compare the vibrational properties obtained for a variety of complexes with experimental data as well as other first-principles calculations

in the literature. Finally, we discuss the results.

II. METHODOLOGY

A. Ground State Description

In this work, we use the fully self-consistent *ab-initio* code SIESTA^{15,16}. The electronic energy is obtained from density-functional theory (DFT)^{17,18} within the local density approximation. The exchange-correlation potential is that of Ceperley-Alder¹⁹ as parameterized by Perdew and Zunger.²⁰ Norm-conserving pseudopotentials²¹ in the Kleinman-Bylander form²² are used to remove the core electrons from the calculations.

The valence electron wavefunctions are described with numerical linear combinations of atomic orbitals (LCAO) of the Sankey type,²³ but generalized to be arbitrarily complete with the inclusion of multiple-zeta orbitals and polarization states.²⁴ These orbitals are numerical solutions of the free atom with the appropriate pseudopotential, and are extrictly zero beyond some cutoff radius. This makes the calculation of the Kohn-Sham hamiltonian to scale linearly with the number of atoms,^{15,16} allowing calculations in very large systems with a modest computational cost.

In the present work, the basis sets include single-zeta (SZ), double-zeta (DZ), double-zeta plus polarization (DZP), and triple-zeta plus polarization (TZP). A DZP basis includes two sets of *s* and *p*'s plus one set of *d*'s on Si, O, C or B, two *s*'s and one set of *p*'s on H. The radial cutoff of the atomic orbitals was determined as described in Ref. 24, with an energy shift of 0.5 Ry, and a split-norm of 0.15 for all the species except H, for which the split-norm was 0.5. The charge density is projected on a real space grid with an equivalent cutoff of 90 to 150 *Ry* to calculate the exchange-correlation and Hartree potentials. The host crystal is represented by a periodic supercell of 64 host atoms, and the **k**-point sampling is reduced to the Γ point. This restriction appears to be quite sufficient for the calculation of vibrational spectra. Tests have been performed for selected defects in a 128 host atoms cell and the results are within a few wavenumbers of those obtained in the 64 host atoms cell.

In order to determine the equilibrium structure of the defects studied, we have relaxed all the atomic coordinates with a conjugate gradient algorithm, reaching a tolerance in the forces of $F_{max} < 0.01 \text{ eV}/\text{\AA}$. The dynamical matrix for the whole cell is computed (see below)

from this ground state and its eigenfrequencies and eigenmodes obtained.

B. Linear Response Theory

A new implementation of DFPT has been developed to compute the electronic response to *infinitesimal* atomic displacements. As is well known from the “ $2n + 1$ ” theorem in quantum mechanics,²⁵ the first-order change of the electronic wavefunction in a perturbative expansion allows the computation of the second-order change in the energies. This implies that only the properties of the unperturbed ground state are needed to obtain the linear response of the system. The extension of this theorem to DFT is that the knowledge of the first-order change in the electronic density determines variationally the second-order change in the energy. In this way, we obtain analytically the dynamical matrix from the gradient of the density relative to atomic displacement and, from it, the vibrational properties, without physically displacing any atom.

We describe briefly here the key points of our formulation. A complete report will be published elsewhere.²⁶ The change in the electronic wavefunction is obtained by solving the first-order perturbation expansion of the Schrödinger equation (Sternheimer equation²⁷)

$$\delta \hat{H} \psi_{0,i} + \hat{H}_0 \delta \psi_i = \delta \epsilon_i \psi_{0,i} + \epsilon_{0,i} \delta \psi_i \quad (1)$$

where $\psi_{0,i}$ are the ground state electronic wavefunctions and $\delta \psi_i$ the first order perturbation of ψ_i when an atom is displaced (if we consider atom α , this would be $\partial_\alpha \psi_i$). As we expand these wave functions in terms of atomic orbitals:

$$\psi_{0,i}(\mathbf{r}) = \sum_{\mu} c_{i\mu} \phi_{\mu}(\mathbf{r} - \mathbf{R}_{\mu}) \quad (2)$$

the derivatives can be directly written in terms of the derivatives of the atomic orbitals:

$$\partial_{\alpha} \psi_i(\mathbf{r}) = \sum_{\mu} [\partial_{\alpha} c_{i\mu} \phi_{\mu}(\mathbf{r} - \mathbf{R}_{\mu}) + c_{i\mu} \partial_{\alpha} \phi_{\mu}(\mathbf{r} - \mathbf{R}_{\mu})] . \quad (3)$$

Only the orbitals ϕ_{μ} centered on atom α appear in the last term which is equal to $-\nabla \phi_{\mu}(\mathbf{r} - \mathbf{R}_{\mu})$. The change in the coefficients, $\partial_{\alpha} c_{i\mu}$, is obtained from equation 1. $\partial \psi_i$ is then used to compute the perturbation in the electronic density

$$\partial_{\alpha} \rho(\mathbf{r}) = \sum_{\mathbf{i}=1}^{\text{occ}} [\partial_{\alpha} \psi_{\mathbf{i}}^* \psi_{\mathbf{i}} + \psi_{\mathbf{i}}^* \partial_{\alpha} \psi_{\mathbf{i}}] . \quad (4)$$

This allows the computation of the dynamical matrix, by explicit derivation of the forces on all the atoms β in the system (the expressions of which can be found in Refs. 15 and 16 for our approach) with respect to the infinitesimal displacement of one of them (α):

$$(M_\alpha M_\beta)^{1/2} \mathbf{D}_{\alpha\beta} = \frac{\partial^2 E}{\partial \mathbf{R}_\alpha \partial \mathbf{R}_\beta} = \partial_\alpha \mathbf{F}_\beta \quad (5)$$

We remark that only terms up to first order in the electronic wavefunctions appear in the resulting formulas. Note that only the linear effects are obtained in this method, which is consistent with the harmonic approximation implicitly assumed in the diagonalization of the dynamical matrix. Thus, one expects to obtain high-quality frequencies for the vibrational modes that are harmonic, but the frequencies of modes involving large anharmonic contributions will be less accurate. Although phonons with arbitrary $\mathbf{q}$ vector can be obtained in the present approach, here we only calculate vibrations which are periodic with the simulation supercell (*i.e.*, $\mathbf{q} = \Gamma$), since we are interested in LVMs.

III. RESULTS

Tests of the method for free SiH_4 , CO , CO_2 and H_2 lead to very good agreement with experiment (see table I). Using an appropriate basis set reveals to be essential to reproduce accurate frequencies. In most of the cases a DZ set gives good values, but in some configurations a more complete basis is required. This is particularly true for bending modes. Oxygen likes to have polarization orbitals, and thus the frequencies are better when these are included. Note that the vibrational frequencies are more sensitive to the basis set size than the structural properties, such as bond lengths. In general, the largest improvements in the frequencies correspond to going from SZ to DZ, then DZ to DZP, but TZ basis produce only marginal improvements.

A number of defects containing light impurities in c-Si are now considered. These are H at a bond-center (BC) site, H dimers (H_2 and H_2^*), the hydrogenated vacancy (VH_n , $n = 1, 2, 3, 4$) and the saturated divacancy V_2H_6 , the self-interstitial-hydrogen IH_2 complex, the $\{\text{B}, \text{H}\}$ pair, substitutional C, interstitial O, and two charge states of the A-center (oxygen-vacancy complex). These embrace a range of Si-X bonding configurations, with $\text{X}=\text{H}$, C, O and B. In most cases, we have tried different basis sets in order to check, or improve the accuracy of our calculations when the chemical properties are particularly complex. We show

TABLE I: Calculated and measured²⁸ frequencies for free SiH₄, CO, CO₂ and H₂ molecules with various basis sets.

	SZ	SZP	DZ	DZP	TZ	TZP	Expt.
<i>SiH₄</i>							
<i>T₂</i>	2045	2064	2160	2153	2173	2159	2191
<i>A₁</i>	1970	1974	2110	2116	2131	2125	2187
<i>E</i>	800	862	921	929	926	929	975
<i>T₂</i>	701	772	806	818	817	821	914
<i>H₂</i>							
<i>A</i>	3619	3670	4194	4185	4193	4191	4161
<i>CO</i>							
<i>A</i>	1681	1823	1885	2088	1945	2183	2170
<i>CO₂</i>							
<i>A₁</i>	2118	2355	2235	2277	2224	2394	2349
<i>A₂</i>	1107	1216	1200	1241	1209	1331	1333
<i>E</i>	478	558	547	583	560	635	667

frequencies for the DZ and DZP basis sets. Although the diagonalization of the dynamical matrix gives all the (Γ point) modes in the cell, we present here only the stretching and some bending LVMS. We also obtain the eigenvectors which we use to determine the symmetry of the corresponding vibrational modes. Our results are compared with available experimental data, and with theoretical frequencies obtained by other authors using first-principle DFT.

A. H_{BC}, H₂ and H₂^{*}

At the BC site,²⁹ hydrogen exists in the +1 and the 0 charge states. In the latter case, the odd electron does not participate in the bonding but resides in a non-bonding orbital primarily localized on the two Si atoms adjacent to the proton. Chemically, this is a 3-center, 2-electron bond, very much like the type of H bonding occurring in boron hydrides. The bond is somewhat compressed because optimal relaxation (no Si second nearest neighbors) would likely result in a longer Si-H-Si bond and a frequency lower than observed. This

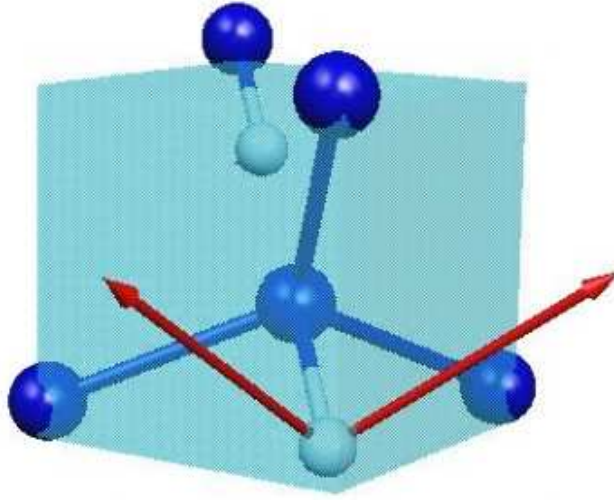


FIG. 1: Calculated structure of H_2^* complex in silicon. Dark spheres are Si atoms, white spheres are H. The two perpendicular arrows represent the H_{AB} wag eigenmodes at 842 cm^{-1} . The twofold degenerate wagging mode for H_{BC} is found at 560 cm^{-1} .

suggests that as H moves along the trigonal axis, it tends to form something like $\text{Si}\dots\text{H-Si}$ then Si-H-Si then $\text{Si-H}\dots\text{Si}$, a process which is highly anharmonic. The calculated frequency is in table II.

Raman⁴⁰ and IR^{33,41} measurements of H_2 in silicon reveal a considerable softening of the stretching mode with respect to the frequency of H_2 in the gas phase. A number of calculations (for a review, see Ref. 39) found the molecule to be stable at the tetrahedral interstitial (T) site. The electron affinity of the Si atoms surrounding H_2 is at least partly responsible for a small charge transfer from H_2 to its Si neighbors, which results in a weakening of the H-H bond. Even though the H-H stretch mode is not expected to be fully harmonic, our calculated frequency is close to the experimental one (table II). Note that the errors relative to experiment in the D_2 and HD frequencies are very different than the error in the H_2 frequency. This is also a clear feature of these frequencies when they are calculated dynamically from the v-v autocorrelation function.⁴²

The trigonal H_2^* defect⁸ consists of one hydrogen atom close to the antibonding (AB) site, and the other near the BC site (see figure 1). The two H atoms are inequivalent. The Si-H_{AB} bond length is slightly longer than the Si-H_{BC} one (we obtain 1.580 and 1.510 Å,

respectively) which gives rise to different stretch frequencies for the two atoms: 2135 cm^{-1} for H_{BC} and 1750 cm^{-1} for H_{AB} . We also obtain two degenerate wagging modes, associated with the H_{BC} atom, at 560 cm^{-1} , and two wagging modes with 839 and 843 cm^{-1} , related to H_{AB} . The latter should be degenerate, but small inaccuracies in the atomic relaxations render them at slightly different frequencies.

TABLE II: Calculated and measured frequencies for H_{BC} (our calculation is spin polarized for H_{BC}^0 and spin averaged for H_{BC}^+), H_2 in the $\langle 100 \rangle$ alignment, and $H_2^* = H_{BC}H_{AB}$. A DZ basis was used for all these complexes. The errors relative to experimental values are in parenthesis. (a) is Ref. 30, (b) is Ref. 31, (c) is Ref. 32, (d) is Ref. 33, (e) is Ref. 34, (f) is Ref. 35, (g) is Ref. 36, (h) is Ref. 37, and (i) is Ref. 38. Were H_2 a classical dumbbell, its wag modes would be at 731 and 860 cm^{-1} (see discussion in Ref. 39).

expt.		this work	other authors		
H _{BC}					
H ⁺ _{BC}	1998 ^a	1891 (−5%)	2203 ^b (+10%)	2210 ^c (+11%)	
H ⁰ _{BC}	—	1813	1768 ^b	1945 ^c	
H ₂ in Si					
H ₂	3618 ^d	3549 (−2%)	3607 ^e (+0%)	3396 ^f (−6%)	3260 ⁱ (−9%)
DH	3265 ^d	3081 (−6%)	3129 ^e (−4%)		
D ₂	2643 ^d	2511 (−5%)	2559 ^e (−3%)		
	2062 ^g	2135 (+3%)	2164 ^g (+5%)	2100 ^h (+2%)	1945 ⁱ (−5%)
H [*] ₂	1838 ^g	1750 (−5%)	1844 ^g (+0%)	1500 ^h (+18%)	1677 ⁱ (−9%)
	817 ^g	843/839 (+3%)	1002 ^g (+22%)		711 ⁱ (−13%)

B. Hydrogen and native defects

A considerable number of IR and Raman lines are related to H-intrinsic defect complexes. It has been noted^{43,44} that vibrational modes above 2000 cm^{-1} are mainly related to H in vacancies, while those lines below 2000 cm^{-1} are predominant for the H-self-interstitial systems or H at AB sites. A large number of geometrical configurations may lead to very similar vibrational lines, making it difficult to identify these defects unambiguously. As noted

by other groups^{2,45,46,47}, the stretching frequencies in VH_n ($n = 1, 2, 3, 4$) systems increases with n due to the repulsive H-H interaction. Thus, the highest IR line is that of VH_4 . The Si-H bonds point toward the center of the vacancy along the trigonal axes.

In our calculations (table III), VH has monoclinic symmetry, and the H oscillates parallel to the $\langle 111 \rangle$ direction. In the orthorhombic VH_2 , the two equivalent H have stretching modes along the $\langle 100 \rangle$ and $\langle 001 \rangle$ directions. The frequencies for these modes are 2121 and 2144 cm^{-1} respectively. VH_3 has C_{3v} symmetry. The A singlet involves the movement of the three H atoms towards the vacancy, while in the twofold degenerate E mode one of the atoms moves in opposition. VH_4 has T_d symmetry. In addition to the threefold degenerate T_2 mode at 2205, we obtain an IR-inactive singlet A_1 mode at 2265 cm^{-1} .

The vibrational modes of V_2H_6 are almost identical to those of VH_3 : The fully saturated divacancy behaves very much like two weakly coupled VH_3 complexes. The A_2 singlet at 2176 cm^{-1} induces a dipole along the $\langle 111 \rangle$ direction. In addition to this mode and the IR-active E doublet, we obtain two IR-inactive modes at 2186 cm^{-1} and 2134 cm^{-1} .

The IH_2 complex⁵⁰ has two equivalent and weakly coupled hydrogen atoms, which yields two very similar stretching frequencies. Uniaxial stress measurements show that the two hydrogen atoms are equivalent. Our relaxed structure has almost C_{2v} symmetry, with the A mode higher than the B mode, confirming early results⁵⁰. The deviation from perfect symmetry is due to the finite tolerance in the geometry optimization. This deviation is seen when comparing the IHD and IDH complexes: they should be identical but we find their frequencies to be off by 2 cm^{-1} . Note that we reproduce the correct ordering for the bending modes of IH_2 at 737 and 732 cm^{-1} (table IV).

C. Oxygen, Carbon and Boron in Silicon

Oxygen is a well-known impurity which is especially important in Czochralski-grown Si, and a considerable amount of effort was focused in understanding its properties.⁵¹ We have computed the LVM frequencies for interstitial oxygen (O_i) and two charge states of the vacancy-oxygen complex (A-center). The results are in table V. Frequencies for O_i were computed with the oxygen placed at the BC site, where the probability of finding this delocalized atom is maximum, and the classical harmonic potential can better describe the local modes. The IR-active A_{2u} mode corresponds to the asymmetric-stretching mode,

while the A_{1g} is the symmetric one. E_u mode involves the movement of nearest silicon atoms with no participation of the oxygen⁵². Finally, Table VI shows the triply degenerate mode of substitutional carbon as well as the LVMs associated with the $\{B, H\}$ complex.²

IV. CONCLUSIONS

We have presented a new development of DFPT, using localized atomic wavefunctions as a basis set, and applied it to the study of LVMs for light impurities in silicon. In contrast to other methods, the dynamical matrix is computed analytically without actually displacing any atom from its equilibrium position. The calculations are based on the ground state density matrix as computed with the SIESTA package.

Tests of the method for free molecules (SiH_4 , H_2 , CO , and CO_2) show that this approach is highly accurate in situations where the anharmonic contributions are small. Note that the frequencies are obtained at $T = 0K$ while experimental data are obtained at low, but non-zero, temperatures.

We have used a variety of basis set sizes to describe the electronic wavefunctions. In most cases, a DZ basis is quite sufficient to obtain accurate atomic structures and vibrational frequencies. Larger basis sets such as DZP improve the frequencies in situations that involve more complex chemical bondings. The defects included here are H_{BC} , H_2 , H_2^* , VH_n (with $n=1,2,3,4$), V_2H_6 , IH_2 , the $\{B, H\}$ pair, substitutional C, interstitial O and two charge states of the A center. These defects involve a wide range of bonding configurations.

The average error of the 60 calculated modes relative to experiment is about 2%. In situations where large anharmonic contributions are present, the accuracy of the method decreases somewhat (5 – 6%). This occurs, for example, when H is close to a BC position. However, in most cases the calculated frequencies are in remarkable agreement (0 to 2%) with experimental data, implying that this perturbative approach is totally justified and that the ground state density matrix calculated with SIESTA is very reliable.

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TABLE III: Calculated and measured frequencies for stretching modes in VH_n ($n = 1, 2, 3, 4$) and V_2H_6 . (a) is Ref. 44, (b) is Ref. 45, and (c) is Ref. 48. The error relative to experiment is in parenthesis. Our frequencies were obtained with a DZP basis. The measured values for the VH_2D , VHD_2 and VD_3 as published in Ref. 44 are now believed to belong to a divacancy complex⁴⁹ and are therefore not listed here.

expt. ^{<i>a</i>}		this work	Ref. ^{<i>b</i>}	Expt. ^{<i>a</i>}		this work	Ref. ^{<i>b</i>}
VH				VH ₄			
<i>A'</i>	2038	1971 (−3%)	2248(+10%)	<i>A</i> ₁	2257 ^{<i>c</i>}	2265 (+0%)	2404(+6%)
VD				<i>T</i> ₂ 2222 2205 (−1%) 2319(+4%)			
<i>A'</i>	1507	1418 (−6%)	1613(+7%)	VH ₃ D			
VH ₂				<i>A</i> ₁	2250	2251 (+0%)	2384(+6%)
<i>A</i> ₁	2144	2163 (+1%)	2316(+7%)	<i>E</i>	2224	2205 (−1%)	2319(+4%)
<i>B</i> ₁	2121	2132 (+1%)	2267(+7%)	<i>A</i> ₁	1620	1594 (−2%)	1677(+3%)
VHD				VH ₂ D ₂			
<i>A'</i>	2134	2135 (−0%)	2292(+7%)	<i>A</i> ₁	2244	2235 (−0%)	2364(+5%)
<i>A'</i>	1555	1551 (−0%)	1641(+5%)	<i>B</i> ₁	2225	2204 (−1%)	2319(+4%)
VD ₂				<i>A</i> ₁	1628	1603 (−1%)	1690(+4%)
<i>A</i> ₁	1564	1552 (−1%)	1658(+6%)	<i>B</i> ₂	1615	1585 (−2%)	1663(+3%)
<i>B</i> ₁	1547	1532 (−0%)	1625(+5%)	VHD ₃			
VH ₃				<i>A</i> ₁	2236	2221 (−1%)	2342(+5%)
<i>A</i> ₁	2185	2158 (−1%)	2318(+6%)	<i>A</i> ₁	1636	1613 (−1%)	1705(+4%)
<i>E</i>	2155	2100 (−2%)	2256(+5%)	<i>E</i>	1616	1584 (−2%)	1664(+4%)
VH ₂ D				VD ₄			
<i>A'</i>		2140	2298	<i>A</i> ₁	no-IR	1623	1721
<i>A''</i>		2101	2256	<i>T</i> ₂	1617	1584 (−2%)	1664(+3%)
<i>A'</i>		1520	1632	V ₂ H ₆			
VHD ₂				<i>A</i> ₁	2190 ^{<i>c</i>}	2186 (−0%)	—
<i>A'</i>		1534	1646	<i>A</i> ₂	2191	2176 (−0%)	—
<i>A''</i>		1509	1619	<i>E</i>	2166 ^{<i>c</i>}	2143 (−1%)	—
VD ₃				<i>E</i>	2165	2134 (−1%)	—
<i>A</i> ₁		1547	1661	15			
<i>E</i>		1510	1619				

TABLE IV: Calculated frequencies with a DZ basis set compared with experimental and other theoretical results for IH₂. (*a*) is Ref. 50 and (*b*) is Ref. 45. The error relative to experiment is in parenthesis.

expt. ^a this work other authors					expt. ^a this work other authors				
IH ₂					ID ₂				
<i>A</i>	1989	2007 (+1%)	2107 ^b (+6%)	2145 ^a (+8%)	1448	1440 (−1%)	1510 ^b (+4%)	1540 ^a (+6%)	
<i>B</i>	1986	2004 (+1%)	2106 ^b (+6%)	2143 ^a (+8%)	1446	1438 (−1%)	1508 ^b (+4%)	1539 ^a (+6%)	
<i>B</i>	748	737 (−1%)		(<i>A</i>) 775 ^a (+3%)		609		590 ^a	
<i>A</i>	743	733 (−1%)		(<i>B</i>) 768 ^a (+3%)		601		583 ^a	
<i>A</i>		716		(<i>B</i>) 736 ^a		566		564 ^a	
<i>B</i>		711		(<i>A</i>) 717 ^a		562		555 ^a	
IHD/IDH									
	expt. ^a	this work				other authors			
	1988	2005/2007 (+1%)				2106 ^b (+6%)	2144 ^a (+8%)		
	1447	1440/1438 (−1%)				1509 ^b (+3%)	1540 ^a (+6%)		
	746	733/736 (−2%)					771 ^a (+3%)		
		714/714					727 ^a		

TABLE V: Calculated and measured LVMs for interstitial O (O_i) and two charge states of the A-center (VO^0 and VO^-). (a) is Ref. 53 for O_i and Ref. 54 for $VO^{(0/-)}$, (b) is Ref. 55, and (c) is Ref. 56. For $VO^{(0/-)}$ a DZP basis was used for O and its Si nearest-neighbors, and a DZ basis for the other Si atoms. For O_i , a DZP basis was used for all the atoms in the cell.

		expt. ^a	this work	Calc ^b	Calc ^c
			D_{3d}	D_{3d}	C_2
O_i	A_{2u}	1136	1131 (−0%)	1184(+4%)	1108(−2%) 1098(−3%)
	A_{1g}	618	607 (−2%)	619(+0%)	621(+0%) 630(+2%)
	E_u	518	538 (+4%)	519(+0%)	518(+0%)
VO^0	B_1	836	861 (+3%)	839 ^a (+0%)	843(+1%)
	A_1	534	546 (+2%)	548 ^a (+3%)	540(+1%)
VO^-	B_1	885	897 (+1%)	872 ^a (−1%)	850(−4%)
	A_1	545	558 (+2%)	532 ^a (−2%)	539(−1%)

TABLE VI: Calculated and measured frequencies for substitutional C and the {B,H} pair in Si. (a) is Ref. 57, (b) is Ref. 58, (c) is Ref. 59, (d) is Ref. 61, (e) is Ref. 62, and (f) is Ref. 60. A DZP basis was used for C and its Si nearest-neighbors, and DZ for the other atoms. For the {B,H} pair, a DZ basis was used for all the atoms.

		expt.	this work	other authors
C_s	T_d	607 ^a	631 (+4%)	662 ^b (+9%)
	A	1903 ^c	1958 (+3%)	1830 ^d (−4%)
{B,H}				1880 ^e (−1%)
	E	652	695 (+6%)	